

1. Global joint venture starts operations as WeEn Semiconductors

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Thank you for your cooperation and understanding,

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NXPS20H100CX



Dual power Schottky diode Rev. 2 — 24 May 2012

Product data sheet

Product profile 1.

1.1 General description

Dual common cathode power Schottky diode designed for high frequency switched mode power supplies in a SOT186A (TO-220F) "full pack" plastic package.

1.2 Features and benefits

- High junction temperature capability
- Isolated package
- Low leakage current

- Negligible switching losses
- Optimised design to give low V_F and high $T_{j(max)}$

1.3 Applications

- DC to DC converters
- Freewheeling diode

- OR-ing diode
- Switched mode power supply rectifier

1.4 Quick reference data

Table 1. **Quick reference data**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	-	100	V
I _{F(AV)}	average forward current	square-wave pulse; $\bar{\delta} = 0.5$; $T_h \le 147$ °C; per diode; see Figure 1; see Figure 2; see Figure 3	-	-	10	Α
I _{O(AV)}	average output current	square-wave pulse; $\delta = 0.5$; T _h ≤ 128 °C; both diodes conducting	-	-	20	Α
Tj	junction temperature		-	-	175	°C
Static charac	cteristics					
V_{F}	forward voltage	$I_F = 10 \text{ A}$; $T_j = 25 \text{ °C}$; see Figure 6	-	-	0.77	V
		$I_F = 10 \text{ A}; T_j = 125 \text{ °C}; \text{ see } \frac{\text{Figure 6}}{}$	-	0.59	0.64	V
I _R	reverse current	$V_R = 100 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$	-	2	4.5	μΑ
		$V_R = 100 \text{ V}; T_j = 125 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$	-	1	6	mA



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	K	cathode	mb	A1
3	A2	anode 2		<u> </u>
mb	n.c.	mb; isolated		sym125
			SOT186A (TO-220F)	

3. Ordering information

Table 3. Ordering information

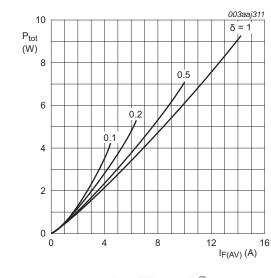
Type number	Package		
	Name	Description	Version
NXPS20H100CX	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	100	V
I _{F(AV)}	average forward current	square-wave pulse; δ = 0.5 ; $T_h \le$ 147 °C; per diode; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	10	Α
I _{O(AV)}	average output current	square-wave pulse; δ = 0.5 ; $T_h \le$ 128 °C; both diodes conducting	-	20	Α
I _{FSM}	non-repetitive peak forward current	sine-wave pulse; $t_p = 10 \text{ ms}$; $T_{j(init)} = 25 \text{ °C}$; see Figure 4	-	250	Α
T _{stg}	storage temperature		-65	175	°C
T _j	junction temperature		-	175	°C



$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_{O} &= 0.516 \text{ V}; \text{ R}_{S} = 0.010 \text{ } \Omega \end{split}$$

Fig 1. Forward power dissipation as a function of average forward current; square waveform; per diode; maximum values

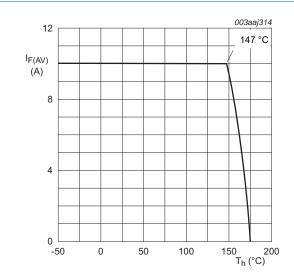


Fig 3. Average forward current as a function of heatsink temperature; per diode; maximum values

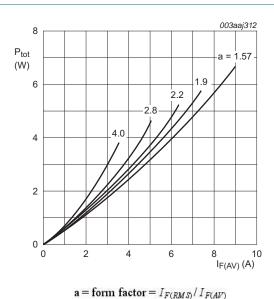


Fig 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; per diode; maximum values

 $V_{\Omega} = 0.516 \text{ V}; R_{S} = 0.010 \Omega$

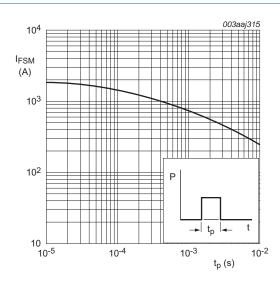
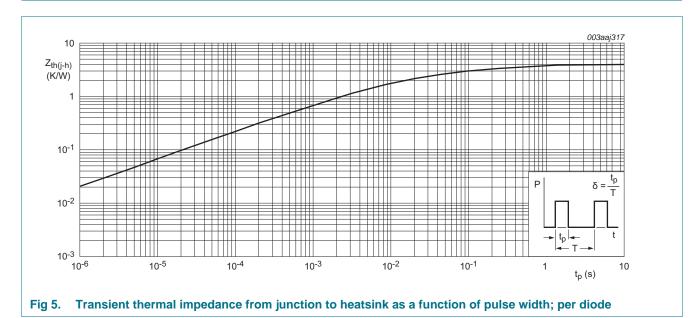


Fig 4. Non-repetitive peak forward current as a function of pulse width; square waveform; per diode; maximum values

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; per diode; see Figure 5	-	-	4	K/W
		with heatsink compound; both diodes conducting	-	-	3.2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W



6. Isolation characteristics

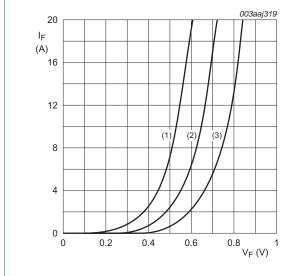
Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(RMS)}$	RMS isolation voltage	50 Hz < f < 60 Hz; sinusoidal waveform; RH ≤ 65 %; clean and dust free; from all terminals to external heatsink	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink; $f = 1 \text{ MHz}$	-	10	-	pF

7. Characteristics

Table 7. Characteristics

D					
Parameter	Conditions	Min	Тур	Max	Unit
racteristics					
forward voltage	$I_F = 8 \text{ A}$; $T_j = 25 \text{ °C}$; see Figure 6	-	-	0.71	V
	$I_F = 10 \text{ A}$; $T_j = 25 \text{ °C}$; see Figure 6	-	-	0.77	V
	$I_F = 16 \text{ A}$; $T_j = 25 \text{ °C}$; see Figure 6	-	-	0.81	V
	$I_F = 20 \text{ A}$; $T_j = 25 \text{ °C}$; see Figure 6	-	-	0.88	V
	$I_F = 8 \text{ A}$; $T_j = 125 \text{ °C}$; see Figure 6	-	0.56	0.58	V
	$I_F = 10 \text{ A}$; $T_j = 125 \text{ °C}$; see Figure 6	-	0.59	0.64	V
	$I_F = 16 \text{ A}; T_j = 125 \text{ °C}; \text{ see } \frac{\text{Figure 6}}{}$	-	0.65	0.68	V
	$I_F = 20 \text{ A}$; $T_j = 125 \text{ °C}$; see Figure 6	-	0.67	0.73	V
reverse current	$V_R = 100 \text{ V; } T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	-	2	4.5	μΑ
	$V_R = 100 \text{ V}; T_j = 125 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$	-	1	6	mΑ
characteristics					
diode capacitance	$f = 1 \text{ MHz}$; $V_R = 10 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 8	-	250	-	pF
	reverse current characteristics	forward voltage $I_F = 8 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \underline{\text{Figure 6}}$ $I_F = 10 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \underline{\text{Figure 6}}$ $I_F = 16 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \underline{\text{Figure 6}}$ $I_F = 20 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \underline{\text{Figure 6}}$ $I_F = 8 \text{ A}; T_j = 125 \text{ °C}; \text{ see } \underline{\text{Figure 6}}$ $I_F = 8 \text{ A}; T_j = 125 \text{ °C}; \text{ see } \underline{\text{Figure 6}}$ $I_F = 10 \text{ A}; T_j = 125 \text{ °C}; \text{ see } \underline{\text{Figure 6}}$ $I_F = 16 \text{ A}; T_j = 125 \text{ °C}; \text{ see } \underline{\text{Figure 6}}$ $I_F = 20 \text{ A}; T_j = 125 \text{ °C}; \text{ see } \underline{\text{Figure 6}}$ $I_F = 20 \text{ A}; T_j = 125 \text{ °C}; \text{ see } \underline{\text{Figure 7}}$ $V_R = 100 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \underline{\text{Figure 7}}$ $V_R = 100 \text{ V}; T_j = 125 \text{ °C}; \text{ see } \underline{\text{Figure 7}}$ $Characteristics$ $diode capacitance$ $f = 1 \text{ MHz}; V_R = 10 \text{ V}; T_j = 25 \text{ °C};$	forward voltage $ \begin{array}{l} I_F=8 \text{ A; } T_j=25 \text{ °C; see } \underline{Figure \ 6} \\ I_F=10 \text{ A; } T_j=25 \text{ °C; see } \underline{Figure \ 6} \\ I_F=16 \text{ A; } T_j=25 \text{ °C; see } \underline{Figure \ 6} \\ I_F=20 \text{ A; } T_j=25 \text{ °C; see } \underline{Figure \ 6} \\ I_F=20 \text{ A; } T_j=125 \text{ °C; see } \underline{Figure \ 6} \\ I_F=8 \text{ A; } T_j=125 \text{ °C; see } \underline{Figure \ 6} \\ I_F=10 \text{ A; } T_j=125 \text{ °C; see } \underline{Figure \ 6} \\ I_F=16 \text{ A; } T_j=125 \text{ °C; see } \underline{Figure \ 6} \\ I_F=20 \text{ A; } T_j=125 \text{ °C; see } \underline{Figure \ 6} \\ I_F=20 \text{ A; } T_j=125 \text{ °C; see } \underline{Figure \ 6} \\ I_F=20 \text{ A; } T_j=125 \text{ °C; see } \underline{Figure \ 6} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text{ °C; see } \underline{Figure \ 7} \\ I_F=100 \text{ V; } T_j=125 \text$	forward voltage	forward voltage



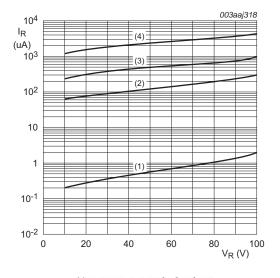
(1) $T_j = 125$ °C; typical values;

(2) T_i = 125 °C; maximum values;

(3) $T_j = 25$ °C; maximum values;

 $V_O = 0.516 \text{ V}; R_S = 0.010 \Omega$

Fig 6. Forward current as a function of forward voltage; per diode



(1) $T_i = 25$ °C; typical values;

(2) T_i = 100 °C; typical values;

(3) T_j = 125 °C; typical values;

(4) $T_j = 150$ °C; typical values

Fig 7. Reverse leakage current as a function of reverse voltage; per diode; typical values

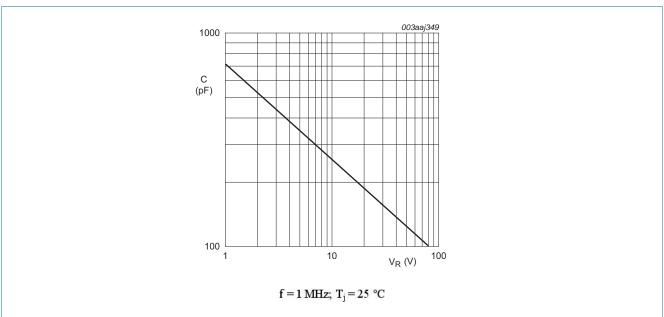


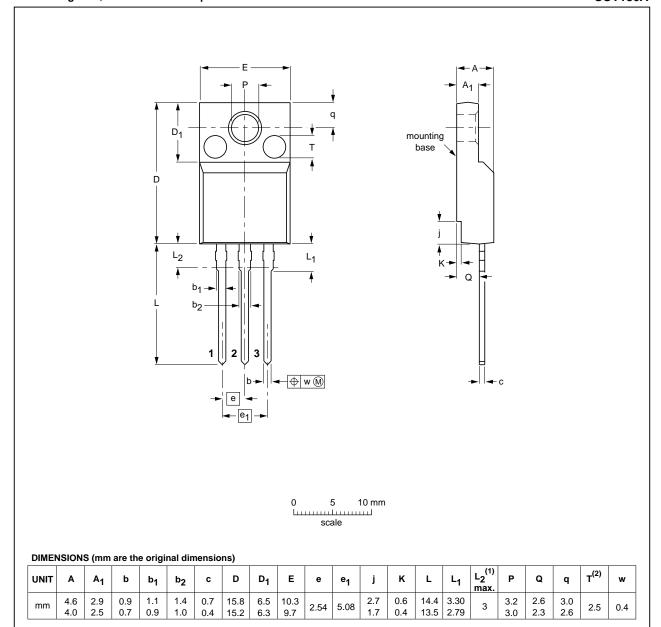
Fig 8. Junction capacitance as a function of applied reverse voltage; per diode; typical values

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8. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are \varnothing 2.5 \times 0.8 max. depth

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	1330E DATE
SOT186A		3-lead TO-220F			-02-04-09 06-02-14

Fig 9. Package outline SOT186A (TO-220F)

NXPS20H100CX

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9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NXPS20H100CX v.2	20120524	Product data sheet	-	NXPS20H100CX v.1
Modifications:	 Status changed from 	om preliminary to product.		
	 Various changes t 	o content.		
NXPS20H100CX v.1	20120420	Preliminary data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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Dual power Schottky diode

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Dual power Schottky diode

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